

LED870-01UP

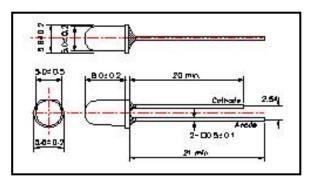
(LN870-01UP) Infrared LED Lamp

LED870-01UP is an AlGaAs LED mounted on a lead frame with a clear epoxy lens. On forward bias, it emits a spectral band of radiation which peaks at 870 nm.

Specifications

1)Product NameInfrared LED Lamp2)Type No.LED870-01UP3)ChipAIGaAs(1)Chip MaterialAIGaAs(2)Peak Wavelength870 nm typ.4)PackageΦ5mm clear molding(2)Resin MaterialEpoxy Resin(3)Lead FrameSoldered

Outer dimension (Unit: mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature	
Power Dissipation	PD	160	mW	Ta=25°C	
Forward Current	lf	100	mA	Ta=25°C	
Pulse Forward Current	lfp	1000	mA	Ta=25°C	
Reverse Voltage	Vr	5	V	Ta=25°C	
Operating Temperature	Topr	-30 ~ +85	°C		
Storage Temperature	Tstg	-30 ~ +100	°C		
Soldering Temperature	Tsol	260	°C		

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us. ‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

Electro-Optical Characteristics [Ta=25°C

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	Vf	IF=50mA		1.50	1.70	V
Reverse Current	IR	Vr=5V			10	uA
Total Radiated Power	Po	IF=50mA	18.0	22.0		mW
Radiant Intensity] IE	IF=50mA	60	90		mW/sr
Peak Wavelength	λΡ	IF=50mA	860	870	880	nm
Half Width	Δλ	IF=50mA		35		nm
Viewing Half Angle	θ 1/2	IF=50mA		±10		deg.
Rise Time	tr	IF=50mA		15		ns
Fall Time	tf	IF=50mA		10		ns

‡Total Radiated Power is measured by Photodyne #500 ‡Radiant Intensity is measured by Tektronix J-6512.